

Thursday, September 25

Room 101 (A)	Room 102 (B)	Room 201A (C)	Room 201B (D)	Room 202A (E)
Area 1: Advanced Gate Stack/Si Processing Science	Area 3: CMOS Devices/Device Physics	Area 12: Spintronic Materials and Devices	Area 5: Advanced Circuits and Systems	Area 7: Photonic Devices and Device Physics
A-3: Nanoscale Characterization (9:00-10:30) Chairs: H. Fukutome (Fujitsu Labs. Ltd.) S. Miyazaki (Hiroshima Univ.)	B-3: FinFET and GAA Devices (9:00-10:35) Chairs: D. Hisamoto (Hitachi, Ltd.) K. Shibahara (Hiroshima Univ.)	C-3: Spintronics (I) (9:00-10:30) Chairs: K. Inomata (NIMS) M. Tanaka (Univ. of Tokyo)	D-3: Imaging Devices (9:00-10:30) Chairs: M. Horiguchi (Renesas Tech. Corp.) T. Komuro (Agilent Technologies Japan, Ltd.)	E-3: Photo Detectors and Sensors (9:00-10:30) Chairs: Y. Lee (Hitachi, Ltd.) M. Sugawara (Fujitsu Labs. Ltd.)
9:00 A-3-1 (Invited) Dopant and Potential Profiling with Atomic Resolution by Scanning Tunneling Microscopy T. Kanayama, M. Nishizawa and L. Bolotov, <i>MIRAI-AIST (Japan)</i>	9:00 B-3-1 Low GIDL Characteristics on Fin-FET with Source/Drain Extension Engineering for 22nm Node Low Power Devices K. Hayashi ¹ , T. Iwamatsu ¹ , R. Tsuchiya ² , K. Ishikawa ¹ , T. Terada ¹ , H. Shinohara ¹ , K. Eikyu ¹ , T. Uchida ¹ , H. Oda ¹ and Y. Inoue ¹ , ¹ Renesas Tech. Corp. and ² Hitachi, Ltd. (Japan)	9:00 C-3-1 Magnetic Properties of Epitaxial Fe ₃ Si/Ge(111) Layers for Group-IV Semiconductor Spintronic Applications Y. Ando ¹ , K. Kasahara ¹ , K. Ueda ¹ , K. Hamaya ¹ , Y. Nozaki ¹ , T. Sadoh ¹ , Y. Maeda ² , K. Matsuyama ¹ and M. Miyao ¹ , ¹ Kyushu Univ. and ² Kyoto Univ. (Japan)	9:00 D-3-1 (Invited) The Dynamic-Range Enhancement Technologies for CMOS Image Sensors S. Sugawa ¹ , N. Akahane ¹ , S. Adachi ² and K. Mizobuchi ² , ¹ Tohoku Univ. and ² Texas Instruments Japan (Japan)	9:00 E-3-1 Characterization of Ge Photodetectors Fabricated on Vicinal Si Substrate K. Terano and S. Yokoyama, <i>Hiroshima Univ. (Japan)</i>
9:30 A-3-2 1-nm Spatial Resolution in Carrier Mapping of Ultra-Shallow Junctions by Scanning Spreading Resistance Microscopy L. Zhang, H. Tanimoto, K. Adachi, N. Yasutake and A. Nishiyama, <i>Toshiba Corp. (Japan)</i>	9:20 B-3-2 Physical and Electrical Design of FinFET based SRAM Bitcell for 22nm Node and Below S. C. Song ¹ , M. Abu-Rahma ¹ , B. M. Han ¹ , S. S. Yoon ¹ , J. Wang ¹ , W. Yang ² , C. Hu ² and G. Yeap ¹ , ¹ Qualcomm Inc. and ² Univ. of California Berkeley (USA)	9:15 C-3-2 Formation and Characterization of Self-Organized Ferromagnetic Nanostructures in Epitaxially Grown Mn-Doped Ge Thin Films S. Yada ¹ , S. Sugahara ² and M. Tanaka ¹ , ¹ Univ. of Tokyo and ² Tokyo Tech. (Japan)	9:30 D-3-2 Temporal Noise Analysis and its Reduction Method in CMOS Imager Readout Circuit B. C. Kim, J. Jeon and H. Shin, <i>Seoul National Univ. (Korea)</i>	9:15 E-3-2 Optimization of Gold Line and Space Antenna for Silicon-On-Insulator Metal-Oxide-Semiconductor Photodetector H. Satoh and H. Inokawa, <i>Shizuoka Univ. (Japan)</i>

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Room 202B (F)	Room 303 (G)	Room 304 (H)	Room 405 (I)	Room 406 (J)
Area 8: Advanced Material Synthesis and Crystal Growth Technology	Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics	Area 13: Applications of Nanotubes and Nanowires	Area 10: Organic Materials Science, Device Physics, and Applications	
F-3: Advanced Nitride Growth and Structures (9:00-10:30) Chairs: N. Sritirawisarn (Eindhoven Univ. of Tech.) Y. Sakuma (NIMS)	G-3: High-speed Devices and Circuits (9:00-10:15) Chairs: S. Tanaka (NEC Corp.) E. Y. Chang (National Chiao Tung Univ.)	H-3: Carbon Nano Devices (9:15-10:30) Chairs: K. Matsumoto (Osaka Univ.) K. Ishibashi (RIKEN)	I-3: Organic Photovoltaic Device (9:15-10:30) Chairs: S. Aramaki (Mitsubishi Chemical Group Sci. & Tec. Res. Center, Inc. (MCRCC)) K. Fujita (Kyushu Univ.)	
9:00 F-3-1 (Invited) Low Temperature Epitaxial Growth of Semiconductors on Metal Substrates H. Fujioka, <i>Univ. of Tokyo (Japan)</i>	9:00 G-3-1 An 85-GHz Distributed Amplifier with 15.5-dBm Output Saturated Power using 0.1- μ m InP HEMTs Y. Nakasha ¹ , M. Sato ² , T. Ohki ² , T. Takahashi ¹ , K. Makiyama ¹ , Y. Kawano ¹ , T. Suzuki ¹ and N. Hara ¹ , ¹ Fujitsu Ltd. and ² Fujitsu Labs. Ltd. (Japan)		9:15 I-3-1 Semitransparent Inverted Organic Photovoltaic Cells with Laminated Top Electrode J. Y. Lee, S. T. Connor, Y. Cui and P. Peumans, <i>Stanford Univ. (USA)</i>	
9:30 F-3-2 Growth of InN on Patterned Sapphire Substrate and its Characterization H. Song, D. W. Kim, S. M. Jeong, Y. M. Lee, J. S. Kim and C. R. Lee, <i>Chonbuk National Univ. (Korea)</i>	9:15 G-3-2 Improved Bias Stability of the RTD-Pair Oscillators Integrated on an AlN Ceramic Substrate K. Maezawa ¹ , N. Kamegai ² , S. Kishimoto ² , T. Mizutani ² and K. Akamatsu ³ , ¹ Univ. of Toyama, ² Nagoya Univ. and ³ Nippon Mining and Metals Co., Ltd. (Japan)	9:15 H-3-2 Low-Energy Oxygen Ion Irradiation Effects on Carbon Nanotube Field-Effect Transistors with Passivation Films S. Nagaso ¹ , Y. Ohno ¹ , K. Maehashi ¹ , K. Inoue ¹ , K. Yamamoto ² and K. Matsumoto ^{1,2} , ¹ Osaka Univ. and ² AIST (Japan)	9:30 I-3-2 Solution-Processed Inverted Organic Photovoltaics on Metal Foil Substrates W. Gaynor, J. Y. Lee, S. T. Connor, Y. Cui and P. Peumans, <i>Stanford Univ. (USA)</i>	

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9:50 A-3-3 Carrier Density Mapping of Small n-MOSFET Devices by Vacuum-gap Modulation Scanning Tunneling Spectroscopy L. Bolotov, M. Nishizawa and T. Kanayama, <i>MIRAI-AIST (Japan)</i>	9:40 B-3-3 Gate-All-Around 4-nm Silicon Nanowire Schottky Barrier MOSFET with 1-D NiSi Source/Drain J. W. Peng ^{1,2,3} , S. J. Lee ² , G. C. Albert Liang ² , N. Singh ¹ , C. M. Ng ³ , G. Q. Lo ¹ and D. L. Kwong ¹ , ¹ Inst. of Microelectronics, ² National Univ. of Singapore and ³ Chartered Semiconductor Manufacturing Ltd. (Singapore)	9:30 C-3-3 Huge Magnetoresistance Effect in Semiconductor based Nanostructures with Zinc-blende MnAs Nanoparticles P. N. Hai ¹ , B. Yu ¹ , S. Ohya ^{1,2} and M. Tanaka ^{1,2} , ¹ Univ. of Tokyo and ² JST (Japan)	9:50 D-3-3 Reset Level Boosting in Self-Adaptive APS for Wide Output Swing at a Low Voltage Operation J. Lee, C. Cho and K. Yang, <i>KAIST (Korea)</i>	9:30 E-3-3 Sputtered Mg _x Zn _{1-x} O based Metal-Semiconductor-Metal Ultraviolet Photodetector H. Y. Lee ¹ , M. Y. Wang ² and L. R. Lou ¹ , ¹ National Cheng Kung Univ. and ² National Formosa Univ. (Taiwan)
10:10 A-3-4 Trap Generation in Sc ₂ O ₃ /La ₂ O ₃ High-k Gate Stack by Nanoscale Electrical Stress Y. C. Ong ¹ , D. S. Ang ¹ , S. J. O'Shea ² , K. L. Pey ¹ , C. H. Tung ³ , T. Kawanago ⁴ , K. Kakushima ⁴ and H. Iwai ⁴ , ¹ Nanyang Tech. Univ., ² Inst. of Materials Res. and Eng., ³ Inst. of Microelectronics and ⁴ Tokyo Tech. (Singapore)	10:00 B-3-4 Erbium/Platinum Silicided Gate-All-Around Silicon Nanowire Schottky Source/Drain MOSFETs E. J. Tan ^{1,2,3} , K. L. Pey ¹ , N. Singh ² , G. Q. Lo ² , D. Z. Chi ³ , Y. K. Chin ¹ and L. J. Tang ² , ¹ Nanyang Technological Univ., ² Inst. of Microelectronics and ³ Inst. of Materials Res. and Eng. (Singapore)	9:45 C-3-4 Spin Transport across Indirect Gap Barriers in GaAs-AlGaAs Heterostructures Y. Gyoda, J. Hayafuji, M. Yarimizu, W. Terui, S. Sugahara and H. Munekata, <i>Tokyo Tech. (Japan)</i>	10:10 D-3-4 A CMOS Image Sensor with CDS and Global Shutter for Three-Dimensional Image Processing System K. Makita, K. Kiyoyama, T. Sugimura, T. Fukushima, T. Tanaka and M. Koyanagi, <i>Tohoku Univ. (Japan)</i>	9:45 E-3-4 Using Selective Zn Diffusion to Enhance the Performance of the PD in Monolithically Integrated InP/InGaAs p-i-n PD/HBT W. K. Huang, S. C. Huang, Y. M. Hsin and J. W. Shi, <i>National Central Univ. (Taiwan)</i>

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9:45 F-3-3 Performance Enhancement of a-plane Light-emitting Diodes using InGaN/GaN Superlattices S. C. Ling ¹ , T. C. Wang ¹ , T. S. Ko ¹ , J. R. Chen ¹ , T. C. Lu ¹ , H. C. Kuo ¹ , S. C. Wang ¹ and J. D. Tsay ² , ¹ National Chiao Tung Univ. and ² Industrial Tech. Res. Inst. (Taiwan)	9:30 G-3-3 40 Gbit/s Operation of MOBILE using Only RTDs and its Application to 2-bit Flash ADC H. Kim, K. Lee, Y. Kim and K. Seo, <i>Seoul National Univ. (Korea)</i>	9:30 H-3-3 High-density Horizontally-aligned Growth of Carbon Nanotubes for High-performance Field-effect Transistors Y. Ohno ¹ , D. Phokharatkul ¹ , H. Nakano ² , S. Kishimoto ¹ and T. Mizutani ¹ , ¹ Nagoya Univ. and ² ULVAC, Inc. (Japan)	9:45 I-3-3 Study and Fabrication of Flexible Polymer Solar Cells Y. S. Tsai, W. P. Chu, S. Y. Chen, K. L. Wang and F. S. Juang, <i>National Formosa Univ. (Taiwan)</i>	
10:00 F-3-4 Effects of Inhomogeneous Gain and Loss on Nitride-based Vertical-Cavity Surface Emitting Lasers S. W. Chen, T. T. Kao, C. C. Kao, J. T. Chu, L. F. Lin, H. W. Huang, T. C. Lu, H. C. Kuo and S. C. Wang, <i>National Chiao Tung Univ. (Taiwan)</i>	9:45 G-3-4 A Flip-Chip Assembled Cavity Resonator Oscillator on a Thin-Film Substrate S. Song, Y. Kim, Y. Kwon and K. S. Seo, <i>Seoul National Univ. (Korea)</i>	9:45 H-3-4 Optical Identification and Electrical Characterization of Graphene Transferred from Natural Graphite on Thinner (90nm-thick) SiO ₂ K. Nagashio, T. Nishimura, K. Kita and A. Toriumi, <i>Univ. of Tokyo (Japan)</i>	10:00 I-3-4 Investigation of Buffer Layer Modified by Doping Glycerol for Polymer Photovoltaic Devices T. S. Huang, Y. K. Su and J. S. Fang, <i>National Cheng Kung Univ. (Taiwan)</i>	

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		<p>10:00 C-3-5 A Fundamental Study Toward the Realization of an SPRAM-based Low Power FPGA M. Sekikawa, K. Kiyoyama, T. Fukushima, T. Tanaka and M. Koyanagi, <i>Tohoku Univ. (Japan)</i></p> <p>10:15 C-3-6 Fabrication of a Standby-Power-Free TMR-Based Nonvolatile Memory-in-Logic Circuit Chip with a Spin-Injection Write Scheme S. Matsunaga¹, J. Hayakawa², S. Ikeda¹, K. Miura², T. Endoh¹, H. Ohno¹ and T. Hanyu¹, ¹<i>Tohoku Univ. and</i> ²<i>Hitachi Advanced Res. Lab. (Japan)</i></p>		<p>10:00 E-3-5 Strained and Unstrained InGaAs/InP Quantum-Well Infrared Infrared Photodetectors Prepared by Metal Organic Chemical Vapor Deposition Y. S. Wang^{1,2}, S. T. Chou³, S. Y. Lin^{3,4}, S. J. Chang¹ and W. Lin², ¹<i>National Cheng Kung Univ.</i>, ²<i>LandMark Optoelectronics Corp.</i>, ³<i>Academia Sinica and</i> ⁴<i>National Chiao Tung Univ. (Taiwan)</i></p> <p>10:15 E-3-6 In(Ga)As Quantum Ring Terahertz Photodetector J. H. Lee, J. H. Dai, Y. T. Chang, C. F. Chan and S. C. Lee, <i>National Taiwan Univ. (Taiwan)</i></p>

Break

Short Presentation P-1 (10:45-12:15) Chair: S. Tsujikawa (Sony Corp.)	Short Presentation P-3 (10:45-12:15) Chair: S. Hayashi (Matsushita Electric Industrial Co., Ltd.)	Short Presentation P-2 and P-12 (10:45-12:15) Chairs: Y. Hayashi (NEC Electronics Corp.) S. Ogawa (Selete)	Short Presentation P-5 and P-11 (10:45-12:15) Chairs: T. Matsuoka (Osaka Univ.) H. Tabata (Univ. of Tokyo) K. Ajito (NTT Corp.)	Short Presentation P-7 (10:45-12:15) Chair: H. Yamada (Tohoku Univ.)
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Area 8: Advanced Material Synthesis and Crystal Growth Technology	Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics	Area 13: Applications of Nanotubes and Nanowires	Area 10: Organic Materials Science, Device Physics, and Applications	
<p>10:15 F-3-5 Ultraviolet Distributed Bragg Reflectors Based on AlGaIn/AlN Multilayers Grown by Metalorganic Chemical Vapor Deposition J. R. Chen, S. C. Ling, H. M. Huang, T. S. Ko, T. C. Lu, H. C. Kuo and S. C. Wang, <i>National Chiao Tung Univ. (Taiwan)</i></p>	<p>10:00 G-3-5 Low-Capacitance Low-Voltage Transient Voltage Suppression Circuit by Diode Activated SiGe HBT in SiGe HBT BiCMOS Process S. H. Dai, J. J. Peng, C. C. Chen, C. J. Lin and Y. C. King, <i>National Tsing Hua Univ. (Taiwan)</i></p>	<p>10:00 H-3-5 (Invited) Carbon based Superconducting Nanostructures for Molecular Spintronics Applications V. Bouchiat^{1,2}, J. P. Cleuziou^{1,2}, W. Wernsdorfer¹, T. Ondarcuhu³, M. Monthieux³, C. Girit², O. Naaman², Y. Zhang², M. Crommie², A. Zettl², J. Clarke² and I. Siddiqi², ¹<i>Institut Néel, Berkeley and</i> ²<i>Univ. of California, Berkeley and</i> ³<i>CEMES-Toulouse (France)</i></p>	<p>10:15 I-3-5 Electron Diffusion Simulation of 3D Porous Structure for Dye-Sensitized Solar Cells K. Ogiya¹, C. Lv¹, A. Suzuki¹, R. Sahnoun¹, M. Koyama¹, H. Tsuboi¹, N. Hatakeyama¹, A. Endou¹, H. Takaba¹, C. A. Del Carpio¹, R. C. Dekka², M. Kubo¹ and A. Miyamoto¹, ¹<i>Tohoku Univ. and</i> ²<i>Tezpur Univ. (Japan)</i></p>	

Break

Short Presentation P-8 (10:45-12:15) Chairs: A. Yamada (Tokyo Tech.) A. Endou (Tohoku Univ.)	Short Presentation P-6 (10:45-12:15) Chair: T. Hashizume (Hokkaido Univ.)	Short Presentation P-9 and P-13 (10:45-12:15) Chair: K. Matsumoto (Osaka Univ.)	Short Presentation P-10 (10:45-12:15) Chair: K. Fujita (Kyushu Univ.)	Short Presentation P-4 (10:45-12:15) Chair: M. Moniwa (Renesas Tech. Corp.)
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Break

Main Convention Hall, 2F

15:00 PL-2-1

Bridging Between Science and Engineering
H. Sakaki, Toyota Inst. of Tech., Japan

Break

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Area 1: Advanced Gate Stack/Si Processing Science	Area 3: CMOS Devices/Device Physics	Area 2: Characterization and Materials Engineering for Interconnect Integration	Area 5: Advanced Circuits and Systems	Area 11: Micro/Nano Electromechanical and Bio-Systems (Devices)
A-5: Characterization of High-k Material (16:00-17:00) Chairs: S. Miyazaki (Hiroshima Univ.) K. Shiraishi (Univ. of Tsukuba)	B-5: Advanced Device Optimization and Reliability (16:00-17:20) Chairs: K. Horita (Renesas Tech. Corp.) A. Azuma (Toshiba Corp.)	C-5: Low-k & Damage I (16:00-17:10) Chairs: T. Tatsumi (Sony Corp.) N. Nakano (Keio Univ.)	D-5: MEMS Techniques (16:00-17:10) Chairs: K. Masu (Tokyo Tech.) R. Fujimoto (Toshiba Corp.)	E-5: Bio Imaging & Spectroscopy (16:00-17:15) Chairs: K. Ajito (NTT Corp.) H. Tabata (Univ. of Tokyo)
16:00 A-5-1 Defect Profiling and the Role of Nitrogen in Lanthanum Oxide-capped High-k Dielectrics for nMOS Applications B. J. O'Sullivan ¹ , R. Mitsuhashi ² , H. Okawa ² , N. Sengoku ² , T. Schram ¹ , G. Groeseneken ^{1,3} , S. Biesemans ¹ , T. Nakabayashi ² , A. Ikeda ² and M. Niwa ² , ¹ IMEC, ² Matsushita Electric Co., Ltd. and ³ Katholieke Univ. (Belgium)	16:00 B-5-1 Design and Optimization of Gate Sidewall Spacers to Achieve 45nm Ground Rule for High-performance Applications T. Miyashita ¹ , K. Ookoshi ² , A. Hatada ² , K. Ikeda ¹ , Y. S. Kim ¹ , M. Nishikawa ² , T. Sakoda ¹ , K. Hosaka ¹ and H. Kurata ¹ , ¹ Fujitsu Labs. Ltd. and ² Fujitsu Microelectronics Ltd. (Japan)	16:00 C-5-1 Molecular Dynamics Simulations of Low-k SiOCH Film Etching by Fluorocarbon Plasmas A. Suzuki ¹ , M. Isobe ¹ , S. Kobayashi ² , M. Fukasawa ² , T. Tatsumi ² and S. Hamaguchi ¹ , ¹ Osaka Univ. and ² Sony Corp. (Japan)	16:00 D-5-1 (Invited) Current Status and Topics of MEMS Sensors K. Maenaka, <i>Univ. of Hyogo (Japan)</i>	16:00 E-5-1 (Invited) THz-wave Generation and Applications K. Kawase ^{1,2} , T. Shibuya ^{1,2} and K. Suizu ¹ , ¹ Nagoya Univ. and ² RIKEN (Japan)

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F-5: Quantum Dots (16:00-17:15) Chairs: B. W. Wessels (Northwestern Univ.) M. Kobayashi (Waseda Univ.)	G-5: GaN Electron Devices and Characterization (16:00-17:15) Chairs: Y. Ohno (Univ. of Tokushima) S. Kuroda (Eudyna Devices Inc.)	H-5: Si-Based Nanowire Devices (16:00-17:15) Chairs: J. Motohisa (Hokkaido Univ.) I. Shorubalko (ETH)	I-5: Organic Electronics & Photonics (16:00-17:15) Chairs: Y. Majima (Tokyo Tech.) K. Kato (Niigata Univ.)	J-5: Flash Memory II (16:00-17:10) Chairs: Y. Shimamoto (Hitachi, Ltd.) Y. C. Chen (Macronix International Co., Ltd.)
16:00 F-5-1 (Invited) InAs/InP Quantum Dots, Dashes and Ordered Arrays N. Sritirawisarn and R. Nötzel, <i>Eindhoven Univ. of Tech. (Netherlands)</i>	16:00 G-5-1 (Invited) GaN HEMTs "Present Status and Future Prospect" T. Kikkawa ¹ and S. Nakajima ² , ¹ Fujitsu Ltd. and ² Eudyna Devices Inc. (Japan)	16:00 H-5-1 (Invited) Device and Technology Platform with Silicon Nanowire G. Q. Lo, N. Singh, S. C. Rustagi, K. D. Buddharaju, N. Balasubramanian and D. L. Kwong, <i>Inst. of Microelectronics (Singapore)</i>	16:00 I-5-1 (Invited) Novel Image Sensor with Organic Photoconductive Films S. Aihara, <i>NHK Sci. and Tech. Res. Labs. (Japan)</i>	16:00 J-5-1 (Invited) Three Dimensional Flash Memory with Bit Cost Scalable Technology for the Future Ultra High Density Storage Devices H. Aochi ¹ , M. Kito ¹ , Y. Fukuzumi ¹ , M. Kido ¹ , H. Tanaka ¹ , Y. Matsuoka ¹ , Y. Komori ¹ , M. Ishiduki ¹ , Y. Nagata ² , R. Katsumata ¹ , Y. Iwata ¹ and A. Nitayama ¹ , ¹ Toshiba Corp. and ² Toshiba Information Systems Corp. (Japan)

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16:20 A-5-2 Chemical Bonding-Induced Dipole at the HfO ₂ /Si Interface N. Miyata ^{1,2} , Y. Abe ^{1,2} and T. Yasuda ¹ , ¹ AIST and ² Musashi Inst. of Tech. (Japan)	16:20 B-5-2 Hot-Carrier AC Lifetime Enhancement due to Wire Resistance Effect (WRE) in 45nm CMOS Circuits N. Mizuguchi, K. Takeuchi, H. Tobe, P. Lee and K. Ishibashi, <i>Renesas Tech. Corp. (Japan)</i>	16:20 C-5-2 Low-k Film Damage-Resistant CO Chemistry-based Ash Process for Low-k/Cu Interconnection in Flash Memory Devices J. Lee ¹ , W. Park ¹ , D. H. Kim ¹ , K. Shin ¹ , J. Choi ¹ and I. Chung ² , ¹ Samsung Electronics Co., Ltd. and ² Univ. of Sungkyunkwan (Korea)	16:30 D-5-2 Self-Assembly for Heterogeneous Integration with Lateral Interconnections Extending over MEMS and LSI Chips T. Konno, T. Fukushima, R. Kobayashi, T. Tanaka and M. Koyanagi, <i>Tohoku Univ. (Japan)</i>	16:30 E-5-2 Microwave Imaging via Beamforming for Early Breast Cancer Detection with Adaptive Antenna Array Y. Kayaba ¹ , X. Xiao ^{1,2} , S. Kubota ¹ , N. Sasaki ¹ and T. Kikkawa ¹ , ¹ Hiroshima Univ. and ² Tianjin Univ. (Japan)
16:40 A-5-3 Photoemission Study of Chemical Bonding Features and Electronic States of Ultrathin HfTi _x O _y /Pt System A. Ohta ¹ , H. Murakami ¹ , S. Higashi ¹ , S. Miyazaki ¹ , M. Tanioku ² , M. Horikawa ² and A. Ogishima ² , ¹ Hiroshima Univ. and ² Elpida Memory Inc. (Japan)	16:40 B-5-3 Stress Memorization Technique (SMT) for pMOS by Dopant Confinement Layer (DCL) H. Ohta ¹ , K. Ikeda ¹ , H. Fukutome ¹ , M. Tajima ² , K. Okabe ² , K. Ohkoshi ² and S. Satoh ¹ , ¹ Fujitsu Labs. Ltd. and ² Fujitsu Microelectronics Ltd. (Japan)	16:40 C-5-3 (Invited) Plasma Physics for Reducing PID in Nano-structure Patternings T. Makabe, T. Ohba and T. Yagisawa, <i>Keio Univ. (Japan)</i>	16:50 D-5-3 Method for Extracting RF Characteristics of CMOS-MEMS Inductors K. Kuwabara ¹ , K. Ushiyama ² , N. Sato ¹ , H. Morimura ¹ , J. Kodate ¹ and H. Ishii ¹ , ¹ NTT Corp. and ² Shibaura Inst. of Tech. (Japan)	16:45 E-5-3 Confocal Imaging for Breast Cancer Detection using UWB Antenna Array on Si S. Kubota ¹ , X. Xiao ² , N. Sasaki ¹ , Y. Kayaba ¹ , K. Kimoto ¹ , W. Moriyama ¹ and T. Kikkawa ¹ , ¹ Hiroshima Univ. and ² Tianjin Univ. (Japan)

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Room 202B (F)	Room 303 (G)	Room 304 (H)	Room 405 (I)	Room 406 (J)
Area 8: Advanced Material Synthesis and Crystal Growth Technology	Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics	Area 13: Applications of Nanotubes and Nanowires	Area 10: Organic Materials Science, Device Physics, and Applications	Area 4: Advanced Memory Technology
16:30 F-5-2 Molecular Beam Epitaxy of Self-assembled InAs Quantum Dots on (001) and (113)B GaAs Substrates under a Slow Growth Rate Condition T. Takahashi, T. Mukai, K. Morita, T. Kitada and T. Isu, <i>Univ. of Tokushima (Japan)</i>	16:30 G-5-2 V _T -V _{SUB} Characterization of AlGaIn/GaN HFET with Regrown Epilayer on p-GaN C. Y. Hu ¹ , K. Nakatani ¹ , D. Kikuta ² , M. Sugimoto ³ , J. P. Ao ¹ and Y. Ohno ¹ , ¹ Univ. of Tokushima, ² Toyota Central R&D Labs., Inc. and ³ Toyota Motor Corp. (Japan)	16:30 H-5-2 Impact of Quantum Effect on Diffusion Layer Resistance of Si Nanowire MOSFETs D. Hagishima ¹ , K. Matsuzawa ¹ and S. Odanaka ² , ¹ Toshiba Corp. and ² Osaka Univ. (Japan)	16:30 I-5-2 Wavelength-Selectivity of Organic Photoconductive Devices by Wet Process T. Fukuda, M. Komoriya, R. Kobayashi, Y. Ishimaru and N. Kamata, <i>Saitama Univ. (Japan)</i>	16:30 J-5-2 Low Temperature GAA Poly-Si Nanowire TFT SONOS Memory for MLC Application J. Fu ^{1,2} , Y. Jiang ^{1,2} , N. Singh ¹ , C. X. Zhu ^{1,2} , G. Q. Lo ¹ and D. L. Kwong ¹ , ¹ Inst. of Microelectronics and ² National Univ. of Singapore (Singapore)
16:45 F-5-3 Optical Properties of GaSb Type-II Dots by Droplet Epitaxy T. Kawazu ¹ , T. Mano ¹ , T. Noda ¹ , Y. Akiyama ¹ and H. Sakaki ^{1,2} , ¹ NIMS and ² Toyota Technological Inst. (Japan)	16:45 G-5-3 High-Temperature Performance of AlGaIn/GaN HEMT-Compatible Lateral Field Effect Rectifier K. Y. Wong, W. Chen, W. Huang and K. J. Chen, <i>Hong Kong Univ. of Sci. and Tech. (China)</i>	16:45 H-5-3 Impacts of Cross Section Shape and Dimension on Electron Effective Mass in Silicon Nanowires D. Yao ^{1,2} , G. Zhang ² , G. Q. Lo ² and B. Li ¹ , ¹ National Univ. of Singapore and ² Inst. of Microelectronics (Singapore)	16:45 I-5-3 Effect of Space-Charge Field on Injection Properties in Organic Electronics J. Lin, M. Weis, T. Manaka and M. Iwamoto, <i>Tokyo Tech. (Japan)</i>	16:50 J-5-3 Multi-Gate Metal Nano-crystal Memories with TiN Nano-crystals, High-k Blocking Dielectric and High Work Function Gate Electrode C. P. Lu ¹ , C. K. Luo ¹ , B. Y. Tsui ¹ , C. H. Lin ² , P. J. Tzeng ² , C. C. Wang ² and M. J. Tsai ² , ¹ National Chiao Tung Univ. and ² Industrial Tech. Res. Inst. (Taiwan)

Thursday, September 25

Room 101 (A)	Room 102 (B)	Room 201A (C)	Room 201B (D)	Room 202A (E)
Area 1: Advanced Gate Stack/Si Processing Science	Area 3: CMOS Devices/Device Physics	Area 2: Characterization and Materials Engineering for Interconnect Integration	Area 5: Advanced Circuits and Systems	Area 11: Micro/Nano Electromechanical and Bio-Systems (Devices)
	<p>17:00 B-5-4 New High-Voltage and Reliable RF LDMOS Fabricated with Standard Foundry CMOS Technology H. Xiao¹, R. Huang¹, L. Zhang¹, F. Song¹, Y. Ai¹, R. Wang¹, D. Wu¹, H. Liao¹, W. Wong² and Y. Wang¹, ¹<i>Peking Univ. and</i> ²<i>SMIC (China)</i></p>			<p>17:00 E-5-4 In-Situ Surface Infrared Study of DNA Hybridization on Au Island Films Deposited on Si Surfaces A. Hirano-Iwata, K. Tanaka, Y. Kimura and M. Niwano, <i>Tohoku Univ. (Japan)</i></p>

Break

Area 1: Advanced Gate Stack/Si Processing Science	Area 3: CMOS Devices/Device Physics	Area 2: Characterization and Materials Engineering for Interconnect Integration	Area 5: Advanced Circuits and Systems	Area 11: Micro/Nano Electromechanical and Bio-Systems (Devices)
A-6: Source Drain Engineering (17:25-18:45) Chairs: B. Mizuno (UJT Lab. Inc.) Y. Nara (Selete)	B-6: Advanced Booster Technologies (17:25-18:45) Chairs: S. Hayashi (Matsushita Electric Industrial Co., Ltd.) T. Tanaka (Fujitsu Micro-electronics Ltd.)	C-6: Low-k & Damage II (17:25-18:45) Chairs: S. Ogawa (Selete) M. Matsuura (Renesas Tech. Corp.)	D-6: Power Devices (17:25-18:45) Chairs: T. Komuro (Agilent Technologies Japan, Ltd.) H. Yamauchi (Samsung Electronics Co., Ltd.)	E-6: CMOS Based Bio Sensor (17:25-18:40) Chairs: K. Sawada (Toyohashi Univ. of Tech.) M. Sasaki (Toyota Technological Inst.)

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Room 202B (F)	Room 303 (G)	Room 304 (H)	Room 405 (I)	Room 406 (J)
Area 8: Advanced Material Synthesis and Crystal Growth Technology	Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics	Area 13: Applications of Nanotubes and Nanowires	Area 10: Organic Materials Science, Device Physics, and Applications	Area 4: Advanced Memory Technology
	<p>17:00 G-5-4 GaN Schottky Diodes for Microwave Power Rectification K. Takahashi¹, J. P. Ao¹, Y. Ikawa¹, C. Y. Hu¹, H. Kawai², N. Shinohara³, N. Niwa⁴ and Y. Ohno¹, ¹<i>Univ. of Tokushima</i>, ²<i>POWDEC K.K.</i>, ³<i>Univ. of Kyoto</i> and ⁴<i>Kajima Corp. (Japan)</i></p>	<p>17:00 H-5-4 Uniaxially Strained SiGe/Si Core/Shell Nanowire pFETs Integrated on Bulk Si with Ni_xSi_yGe_{1-x-y} Source and Drain Contacts Y. Jiang^{1,2}, N. Singh¹, T. Y. Liow¹, P. C. Lim³, S. Tripathy³, S. A. Oh³, G. Q. Lo¹, D. S. H. Chan² and D. L. Kwong¹, ¹<i>Inst. of Microelectronics</i>, ²<i>National Univ. of Singapore</i> and ³<i>Inst. of Materials Res. and Eng. (Singapore)</i></p>	<p>17:00 I-5-4 Refractive Index along the Molecular Long Axis of an Orthorhombic Thiophene/Phenylene Co-Oligomer Crystal T. Yamao, K. Yamamoto, T. Inoue, Y. Okuda, Y. Taniguchi and S. Hotta, <i>Kyoto Inst. of Tech. (Japan)</i></p>	

Break

Area 8: Advanced Material Synthesis and Crystal Growth Technology	Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics	Area 13: Applications of Nanotubes and Nanowires	Area 10: Organic Materials Science, Device Physics, and Applications	Area 4: Advanced Memory Technology
F-6: Si and Related Materials (17:25-18:40) Chairs: H. Yamaguchi (NTT Corp.) A. Endou (Tohoku Univ.)	G-6: GaN Electron Devices and Characterization (17:25-18:40) Chairs: Y. Ohno (Univ. of Tokushima) S. Kuroda (Eudyna Devices Inc.)	H-6: III-V Nanowire (17:25-18:40) Chairs: K. Tateno (NTT Corp.) Y. Ohno (Nagoya Univ.)	I-6: Organic Materials & Characterization (17:25-18:40) Chairs: K. Fujita (Kyushu Univ.) C. K. Song (Dong-A Univ.)	J-6: Flash Memory III (17:25-18:45) Chairs: R. Shen (eMemory Tech. Inc.) M. Moniwa (Renesas Tech. Corp.)

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Room 101 (A)	Room 102 (B)	Room 201A (C)	Room 201B (D)	Room 202A (E)
Area 1: Advanced Gate Stack/Si Processing Science	Area 3: CMOS Devices/Device Physics	Area 2: Characterization and Materials Engineering for Interconnect Integration	Area 5: Advanced Circuits and Systems	Area 11: Micro/Nano Electromechanical and Bio-Systems (Devices)
17:25 A-6-1 Self-limiting Growth Behavior of Epitaxial NiSi ₂ and its Impact on Controlled Silicidation of Metal Source/Drain in Silicon Nanowire MOSFETs S. Migita, Y. Morita, N. Taoka, W. Mizubayashi and H. Ota, <i>AIST (Japan)</i>	17:25 B-6-1 High Mobility SiGe Channel pMOSFETs Epitaxially Grown on Si (100) Substrates with HfSiO ₂ High-k Dielectric and Metal Gate J. Oh ¹ , P. Majhi ¹ , C. Y. Kang ¹ , R. Jammy ¹ , R. Joe ² , T. Sugawara ² , Y. Akasaka ² , T. Kaitsuka ² , T. Arikado ² and M. Tomoyasu ² , ¹ SEMATECH and ² Tokyo Electron Ltd. (USA)	17:25 C-6-1 Diagnostics of Plasma Induced Damages on Low-k SiOCH Films S. Takashima ¹ , R. Saito ¹ , S. Uchida ¹ , K. Takeda ¹ , M. Fukasawa ² , K. Oshima ² , K. Nagahata ² , T. Tatsumi ² and M. Hori ^{1,3} , ¹ Nagoya Univ., ² Sony Corp. and ³ CREST-JST (Japan)	17:25 D-6-1 (Invited) Modeling of High-Voltage MOSFETs for Device/Circuit Optimization M. Miura-Mattausch, M. Yokomichi, N. Sadachika, Y. Oritsuki, T. Sakuda, M. Miyake, T. Kajiwara, H. Kikuchihara, U. Feldmann and H. J. Mattausch, <i>Hiroshima Univ. (Japan)</i>	17:25 E-6-1 (Invited) FET-based Biosensors for Detection of Biomolecules J. K. Shin ¹ , D. S. Kim ² , H. K. Lyu ¹ and G. Lim ³ , ¹ Kyungpook National Univ. ² Samsung Electronics Co., Ltd. and ³ POSTECH (Korea)

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Room 202B (F)	Room 303 (G)	Room 304 (H)	Room 405 (I)	Room 406 (J)
Area 8: Advanced Material Synthesis and Crystal Growth Technology	Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics	Area 13: Applications of Nanotubes and Nanowires	Area 10: Organic Materials Science, Device Physics, and Applications	Area 4: Advanced Memory Technology
17:25 F-6-1 First-principles Analysis of Indirect-to-Direct Band Gap Transition of Ge Under Tensile Strain Y. Hoshina, K. Iwasaki, A. Yamada and M. Konagai, <i>Tokyo Tech. (Japan)</i>	17:25 G-6-1 (Invited) Failure Mechanisms of GaN-based Transistors in On-and Off- State E. Zanoni ¹ , G. Meneghesso ¹ , C. Dua ² , M. Peroni ³ and M. Uren ⁴ , ¹ Univ. of Padova, ² Alcatel-Thales III-V Lab., ³ Selex SI and ⁴ QinetiQ Ltd. (Italy)	17:25 H-6-1 (Invited) Tunable Few Electron Double Dots in InAs Nanowires I. Shorubalko ¹ , A. Pfund ¹ , S. Gustavsson ¹ , T. Choi ¹ , R. Leturcq ^{1,2} and K. Ensslin ¹ , ¹ ETH Zürich and ² IEMN-CNRS UMR 8520 (Switzerland)	17:25 I-6-1 Effect of Regioregularity and Alkyl Chain Length on the Depletion Layer Width Formed at the Interface of Al and Poly (3-Alkylthiophene) V. Singh, S. S. Pandey, W. Takashima and K. Kaneto, <i>Kyushu Inst. of Tech. (Japan)</i>	17:25 J-6-1 Numerical Simulation of the Read Disturb Behavior on the ONO Scaling Margin in SONOS Flash Memory C. H. Lee ^{1,2} , C. W. Wu ¹ , S. W. Lin ¹ , T. H. Yeh ¹ , S. H. Gu ¹ , K. F. Chen ¹ , Y. J. Chen ¹ , J. Y. Hsieh ¹ , I. J. Huang ¹ , N. K. Zous ¹ , T. T. Han ¹ , M. S. Chen ¹ , W. P. Lu ¹ , K. C. Chen ¹ , T. Wang ^{1,2} and C. Y. Lu ¹ , ¹ Macronix International Co., Ltd and ² National Chiao Tung Univ. (Taiwan)

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Room 101 (A)	Room 102 (B)	Room 201A (C)	Room 201B (D)	Room 202A (E)
Area 1: Advanced Gate Stack/Si Processing Science	Area 3: CMOS Devices/Device Physics	Area 2: Characterization and Materials Engineering for Interconnect Integration	Area 5: Advanced Circuits and Systems	Area 11: Micro/Nano Electromechanical and Bio-Systems (Devices)
17:45 A-6-2 Low Temperature Phosphorus Segregation at NiGe/Ge Interface by "Snowplow" Effect T. Nishimura, S. Sakata, K. Nagashio, K. Kita and A. Toriumi, <i>Univ. of Tokyo (Japan)</i>	17:45 B-6-2 Thin-Metal Inserted Single-phase Ni-FUSI(MISF) and High-k Gate Stack for Productive LSTP CMOS Application Y. Yamamoto ¹ , K. Satoh ¹ , T. Kawahara ¹ , S. Sakashita ¹ , M. Mizutani ¹ , S. Yamanari ¹ , Y. Ariyama ¹ , Y. Miyagawa ¹ , N. Murata ¹ , T. Sakai ¹ , M. Inoue ¹ , J. Yugami ¹ , S. Ogino ¹ , K. Eikyu ¹ , T. Hayashi ¹ , S. Endo ¹ , T. Yamashita ¹ , H. Oda ¹ , Y. Inoue ¹ , H. Fujimoto ² , Y. Sato ² , T. Oosuka ² , A. Tsudumitani ² , Y. Moriyama ² , K. Nakanishi ² , J. Hirase ² , T. Yamada ² , H. Ogawa ² and Y. Mori ² , ¹ <i>Renesas Tech. Corp. and</i> ² <i>Matsushita Electric Industrial Co., Ltd. (Japan)</i>	17:45 C-6-2 Electrical Reliabilities of Highly Cross-Linked Porous Silica Film Y. Kayaba ¹ , K. Kohmura ² , H. Tanaka ² , K. Kinoshita ³ , S. Chikaki ³ and T. Kikkawa ¹ , ¹ <i>Hiroshima Univ.</i> , ² <i>Mitsui Chemicals, Inc. and</i> ³ <i>Selete (Japan)</i>	17:55 D-6-2 (Invited) Power Device Evolution Challenging to Silicon Material Limit A. Nakagawa, Y. Kawaguchi and K. Nakamura, <i>Toshiba Corp. (Japan)</i>	17:55 E-6-2 Development of a CMOS Image Sensor for In-situ Brain Functional Imaging in Freely-moving Mouse A. Tagawa ¹ , A. Higuchi ¹ , T. Sugiyama ¹ , K. Sasagawa ^{1,2} , T. Tokuda ^{1,2} , H. Tamura ^{1,2} , S. Shiosaka ^{1,2} and J. Ohta ^{1,2} , ¹ <i>NAIST and</i> ² <i>CREST-JST (Japan)</i>

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Room 202B (F)	Room 303 (G)	Room 304 (H)	Room 405 (I)	Room 406 (J)
Area 8: Advanced Material Synthesis and Crystal Growth Technology	Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics	Area 13: Applications of Nanotubes and Nanowires	Area 10: Organic Materials Science, Device Physics, and Applications	Area 4: Advanced Memory Technology
17:40 F-6-2 Electrical Characteristics of Ge p-MOSFETs Formed on Si Substrate with Thermal SiON as Gate Dielectric Y. H. Wu, M. L. Wu, J. R. Wu and Y. S. Lin, <i>National Tsing Hua Univ. (Taiwan)</i>	17:55 G-6-2 Precise C-V Analysis of Insulated-gate/AlGaIn/GaN Interfaces M. Miczek ¹ , B. Adamowicz ¹ , C. Mizue ² and T. Hashizume ² , ¹ <i>Silesian Univ. of Tech. and</i> ² <i>Hokkaido Univ. (Poland)</i>	17:55 H-6-2 One-dimensional and Two-dimensional Spectral Diffusion in InP/InAs/InP Core-Multishell Nanowires K. Goto ¹ , M. Ikezawa ¹ , S. Tomimoto ¹ , B. Pal ¹ , Y. Masumoto ¹ , P. Mohan ² , J. Motohisa ² and T. Fukui ² , ¹ <i>Univ. of Tsukuba and</i> ² <i>Hokkaido Univ. (Japan)</i>	17:40 I-6-2 Detection of Catecholamines with Poly(3-aminobenzylamine) Thin Films using Electrochemical-Surface Plasmon Resonance Spectroscopy A. Baba ¹ , T. Mannen ¹ , R. Ishigami ¹ , Y. Ohdaira ¹ , K. Shinbo ¹ , K. Kato ¹ , F. Kaneko ¹ , N. Fukuda ² and H. Ushijima ² , ¹ <i>Niigata Univ. and</i> ² <i>AIST (Japan)</i>	17:45 J-6-2 A Low Voltage Programming Scheme Feasible for 2-Bit Operation of SONOS Flash Memory with Excellent Data Retention J. H. Kuo ¹ , S. S. Chung ¹ , Y. H. Tseng ² , C. S. Lai ² , Y. Y. Hsu ³ , E. Ho ³ , T. Chen ³ , L. C. Peng ³ and C. H. Chu ³ , ¹ <i>National Chiao Tung Univ.</i> , ² <i>Chang Gung Univ. and</i> ³ <i>ProMOS Tech. Inc. (Taiwan)</i>

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Room 101 (A)	Room 102 (B)	Room 201A (C)	Room 201B (D)	Room 202A (E)
Area 1: Advanced Gate Stack/Si Processing Science	Area 3: CMOS Devices/Device Physics	Area 2: Characterization and Materials Engineering for Interconnect Integration	Area 5: Advanced Circuits and Systems	Area 11: Micro/Nano Electromechanical and Bio-Systems (Devices)
18:05 A-6-3 Formation of Low Resistive S/D-Extension using Carborane Molecular Ion Implantation for Sub-45-nm PMOSFET S. Endo, Y. Kawasaki, T. Yamashita, H. Oda and Y. Inoue, <i>Renesas Tech. Corp. (Japan)</i>	18:05 B-6-3 CMOSFET Featuring Atomically Flat Gate Insulator Film/Silicon Interface on (100) Orientation Surface R. Kuroda ¹ , A. Teramoto ¹ , T. Suwa ¹ , Y. Nakao ¹ , S. Sugawa ¹ and T. Ohmi ^{1,2} , ¹ Tohoku Univ. and ² WPI Research Center (Japan)	18:05 C-6-3 Low-k Impact on Circuit Performance Demonstrated in High-Speed LSIs M. Tada ² , N. Inoue ¹ , J. Kawahara ¹ , H. Yamamoto ¹ , F. Ito ¹ , T. Fukai ¹ , M. Ueki ¹ , S. Miyake ¹ , T. Takeuchi ¹ , S. Saito ¹ , M. Tagami ¹ , N. Furutake ¹ , K. Hijioka ¹ , T. Ito ¹ , Y. Shibue ¹ , T. Senou ¹ , R. Ikeda ¹ , N. Okada ¹ and Y. Hayashi ¹ , ¹ NEC Electronics Corp. and ² NEC Corp. (Japan)	18:25 D-6-3 Capability of Electro-thermal Simulation for Automotive Power Application using Novel LDMOS Model T. Kojima ¹ , T. Kajiwara ² , M. Miyake ² , U. Feldmann ² and M. Miura-Mattausch ² , ¹ Toyota Central R&D Labs., Inc. and ² Hiroshima Univ. (Japan)	18:10 E-6-3 A BioCMOS LSI Circuit with Extended-gate FET Sensor Array K. Nakazato, M. Ohura, H. Ozawa and S. Uno, <i>Nagoya Univ. (Japan)</i>
18:25 A-6-4 Schottky-Barrier Height Tuning of Nickel Silicide on Epitaxial Silicon-Carbon Films with High Substitutional Carbon Content P. S. Y. Lim ¹ , R. T. P. Lee ¹ , A. E. J. Lim ¹ , A. T. Y. Koh ¹ , M. Sinha ¹ , D. Z. Chi ² and Y. C. Ye ¹ , ¹ National Univ. of Singapore and ² Inst. of Materials Res. and Eng. (Singapore)	18:25 B-6-4 A Comprehensive Study of Coulomb Scattering Mobility in Short-Channel Process-Induced Strain NMOSFETs W. P. N. Chen ^{1,2} , P. Su ² and K. Goto ¹ , ¹ Taiwan Semiconductor Manufacturing Co., Ltd. and ² National Chiao Tung Univ. (Taiwan)	18:25 C-6-4 Dielectric Reliability of 50 nm ½ Pitch Structures in Aurora® LK S. Demuyne ¹ , H. G. Kim ² , C. Huffman ¹ , M. Darnon ¹ , H. Struyf ¹ , J. Versluijs ¹ , M. Claes ¹ , G. Vereecke ¹ , P. Verdonck ¹ , H. Volders ¹ , N. Heylen ¹ , K. Kellens ¹ , D. De Roest ³ , H. Sprey ³ and G. P. Beyer ¹ , ¹ IMEC, ² Samsung Electronics Co., Ltd. and ³ ASM (Belgium)	18:25 E-6-4 CMOS Optical Polarization Analyzer Chip for μTAS K. Minakawa, H. Yamada, K. Sasagawa, T. Tokuda and J. Ohta, <i>NAIST (Japan)</i>	

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Room 202B (F)	Room 303 (G)	Room 304 (H)	Room 405 (I)	Room 406 (J)
Area 8: Advanced Material Synthesis and Crystal Growth Technology	Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics	Area 13: Applications of Nanotubes and Nanowires	Area 10: Organic Materials Science, Device Physics, and Applications	Area 4: Advanced Memory Technology
17:55 F-6-3 Comparative Stability Characterization of Bottom Gate a-IGZO Thin Film Transistor Grown by R.F and D.C Sputtering S. S. Park ¹ , W. H. Choi ¹ , D. H. Nam ¹ , K. I. Chai ¹ , H. D. Lee ¹ , J. K. Jeong ² , J. S. Oh ³ and G. W. Lee ¹ , ¹ Chungnam National Univ., ² Samsung SDI Co., Ltd. and ³ National Nanofab Center (Korea)	18:10 G-6-3 Near-midgap Deep Levels in MOVPE-grown AlGaIn K. Sugawara, J. Kotani and T. Hashizume, <i>Hokkaido Univ. (Japan)</i>	18:10 H-6-3 Effect of Growth Condition on Well-Arranged InGaIn/GaN Nanocolumns Grown by Selective Area Growth (SAG) of rf-Plasma-Assisted Molecular-Beam Epitaxy H. Sekiguchi ^{1,2} , K. Kishino ^{1,2} and A. Kikuchi ^{1,2} , ¹ Sophia Univ. and ² CREST-JST (Japan)	17:55 I-6-3 A Hybrid Sensing Method Utilizing Surface Plasmon Resonance and Quartz Crystal Microbalance K. Shinbo ¹ , Y. Tsurugai ¹ , K. Aida ¹ , Y. Ohdaira ¹ , A. Baba ¹ , K. Kato ¹ , F. Kaneko ¹ and N. Miyadera ² , ¹ Niigata Univ and ² Hitachi Chemical Co., Ltd. (Japan)	18:05 J-6-3 A New Embedded NVM Thin Film Cell for Low Voltage Applications G. Bossu ^{1,2} , A. Demolliens ^{1,2} , S. Puget ^{1,2} , P. Masson ³ , J. M. Portal ² , R. Bouchakour ² , P. Mazoyer ¹ and T. Skotnicki ¹ , ¹ STMicroelectronics, ² IM2NP and ³ Univ. de Nice Sophia Antipolis (France)
18:10 F-6-4 Carrier Transport Mechanism in Poly-Si TFTs with One-Dimensionally Long Grains S. Fujii, S. Kuroki, X. Zhu, M. Numata, K. Kotani and T. Ito, <i>Tohoku Univ. (Japan)</i>	18:25 G-6-4 On the Stability of Fluorine Ions in AlGaIn/GaN System: a Theoretical Study L. Yuan, M. Wang and K. J. Chen, <i>Hong Kong Univ. of Sci. and Tech. (China)</i>	18:25 H-6-4 Spectroscopy and Imaging of GaAs/InGaAs/GaAs Nanowires Grown by Selective-area Metalorganic Vapor Phase Epitaxy J. Motohisa, M. Fukui, Y. Kobayashi and T. Fukui, <i>Hokkaido Univ. (Japan)</i>	18:10 I-6-4 Statistical Representation of Intrinsic Electronic Tunneling Characteristics through Alkyl Self-Assembled Monolayers H. Song ¹ , N. J. Choi ² , H. Lee ² and T. Lee ¹ , ¹ Gwangju Inst. of Sci. and Tech. and ² Electronics and Telecommunications Res. Inst. (Korea)	18:25 J-6-4 New Charge Pumping Method for Extraction of Nitride Trap Energy Distribution in SONOS Flash Memory W. H. Choi ¹ , S. S. Park ¹ , I. S. Han ¹ , H. M. Kwon ¹ , O. S. Yoo ¹ , M. K. Na ¹ , K. I. Choi ¹ , D. H. Nam ¹ , J. C. Om ² , S. S. Lee ² , H. S. Joo ² , H. D. Lee ¹ and G. W. Lee ¹ , ¹ Chungnam National Univ. and ² Hynix Semiconductor Inc. (Korea)

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Room 101 (A)	Room 102 (B)	Room 201A (C)	Room 201B (D)	Room 202A (E)
Area 1: Advanced Gate Stack/Si Processing Science	Area 3: CMOS Devices/Device Physics	Area 2: Characterization and Materials Engineering for Interconnect Integration	Area 5: Advanced Circuits and Systems	Area 11: Micro/Nano Electromechanical and Bio-Systems (Devices)

19:00-21:00 Rump Session
 Room 101(A) "Can Power Semiconductor Technology Contribute to Sustainable Future?"
 Room 102(B) "Nano-Device and Materials Innovations: What Novel Systems Are You Dreaming of?"

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Room 202B (F)	Room 303 (G)	Room 304 (H)	Room 405 (I)	Room 406 (J)
Area 8: Advanced Material Synthesis and Crystal Growth Technology	Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics	Area 13: Applications of Nanotubes and Nanowires	Area 10: Organic Materials Science, Device Physics, and Applications	Area 4: Advanced Memory Technology

18:25 F-6-5
 Porous Silicon Fabrication for Visible Light Emissions and its White Light Responses
 J. C. Lin¹, W. C. Tsai², K. M. Huang³ and S. J. Wang²,
¹St. John's Univ.,
²National Cheng Kung Univ. and
³Chinese Culture Univ. (Taiwan)

18:25 I-6-5
 Chemisorbed Gold Nanoparticles by Dithiol Molecules Inserted in Alkanethiolated Monolayer Characterized by Scanning Tunneling Microscopy (STM) and Spectroscopy (STS)
 X. Li, Y. Yasutake, K. Kono, N. Kobayashi and Y. Majima, *Tokyo Tech. (Japan)*

19:00-21:00 Rump Session
 Room 101(A) "Can Power Semiconductor Technology Contribute to Sustainable Future?"
 Room 102(B) "Nano-Device and Materials Innovations: What Novel Systems Are You Dreaming of?"